

Supplementary Materials (ESI) for Journal of Materials Chemistry
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Chain scission resists for extreme ultraviolet lithography based on high performance polysulfone-containing polymers†

Kirsten J. Lawrie,^a Idriss Blakey,^a James P. Blinco,^{a‡} Han Hao Cheng,^a Roel Gronheid,^b Kevin S. Jack,^c Ivan Pollentier,^b Michael J. Leeson,^{b,d} Todd R. Yountkin^d and Andrew K. Whittaker^{*a}

^a The University of Queensland, Australian Institute for Bioengineering and Nanotechnology and Centre for Advanced Imaging, St Lucia, 4072, Queensland, Australia. *E-mail: a.whittaker@uq.edu.au

[‡]Current address: Preparative Macromolecular Chemistry, Institut für Technische Chemie und Polymerchemie, Universität Karlsruhe (TH)/Karlsruhe Institute of Technology (KIT), Engesserstr. 18, 76128 Karlsruhe, Germany.

^b Imec, Kapeldreef 75, B-3001 Leuven, Belgium.

^c The University of Queensland, Centre for Microscopy and Microanalysis, St Lucia, 4072, Queensland, Australia..

^d Intel Corporation, Hillsboro, Oregon, 97124 USA.

Supplementary Information

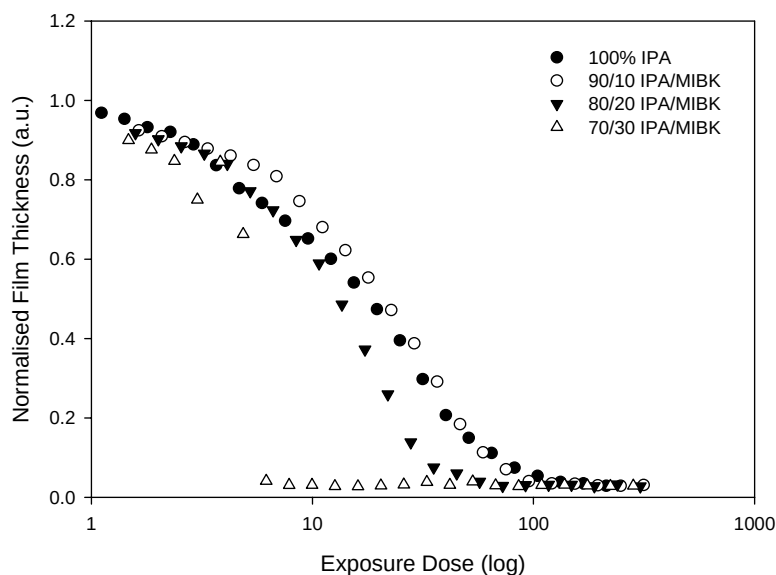


Figure S1. Contrast curves obtained using a variety of solvent developers for material (2).

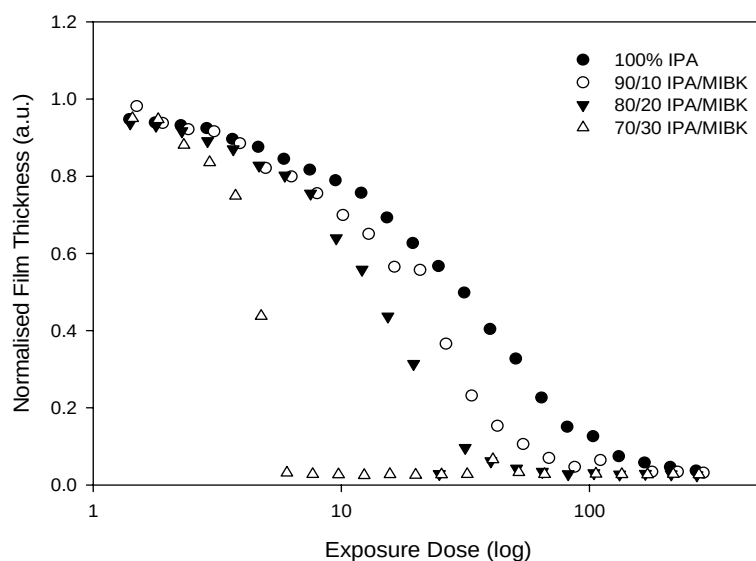


Figure S2. Contrast curves obtained using a variety of solvent developers for material (**3a**).

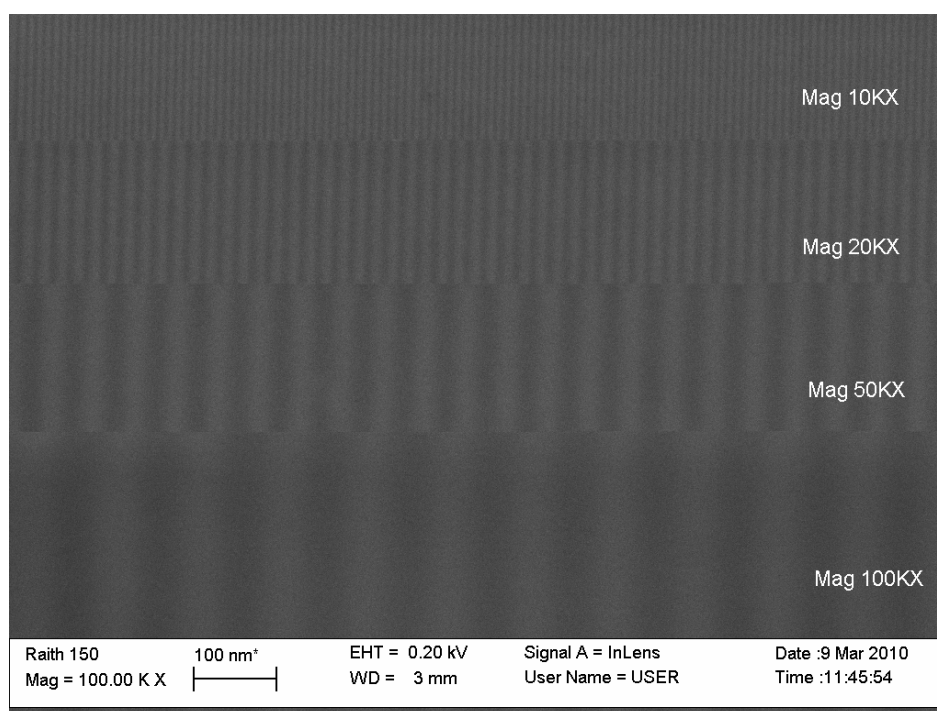


Figure S3. SEM image of poly(1-pentene sulfone) (**2**) 50 nm half pitch lines at magnifications $10\,000\times$ to $100\,000\times$. Image blurring at high magnification results from rapid degradation of the material under the SEM's electron beam.